
Author's Journal Publications

1. **J. Rajpoot**, R. Paul, and S. Verma, "SPICE-Based Compact Model for Voltage-Induced Magnetocapacitance in Magnetic Tunnel Junctions," *IEEE Transactions on Magnetics*, vol. 59, no. 9, pp. 1-8, Sept. 2023, Art no. 7200108, doi: [10.1109/TMAG.2023.3296830](https://doi.org/10.1109/TMAG.2023.3296830).
2. **J. Rajpoot** and S. Verma, "An Advanced Micromagnetic Simulation Framework Enabled by NEGF Formalism for Modeling of STT-MTJ Devices," *IEEE Transactions on Magnetics*, July 2024, (Under revision).
3. **J. Rajpoot** and S. Verma, "Area-Efficient Auto-Write-Terminate Circuit for NV Latch and Logic-In-Memory Applications," *IEEE Transactions on Circuits and Systems II: Express Briefs*, vol. 70, no. 7, pp. 2630-2634, July 2023, doi: [10.1109/TCSII.2023.3242989](https://doi.org/10.1109/TCSII.2023.3242989).
4. A. Kumar, **J. Rajpoot**, S. Verma, "Design space exploration and power optimization of STT MRAM using trimmed fin Asymmetric FinFET" *Microelectronics Journal, Elsevier*, Vol. 149, 2024. Art no. 106238 doi: [10.1016/j.mejo.2024.106238](https://doi.org/10.1016/j.mejo.2024.106238).
5. **J. Rajpoot**, and S. Verma "Compact STT/SHE-MTJ Model with Monte-Carlo In-dependent Thermal Noise," *IOP Journal of Physics: Conference Series*, 2024. (accepted).
6. **J. Rajpoot**, and S. Verma, "Efficient and Reliable Hybrid MTJ/CMOS-Based LiM Architecture using SHE-MTJ," *Journal of Computational Electronics, Springer*. (Under revision).

Author's Conference Publications

- I. **J. Rajpoot, M. Gupta, and S. Verma, "Enhancing the Reliability of Hybrid MTJ/CMOS Circuits with Auto Write Termination,"** *2023 IEEE International Symposium on the Physical and Failure Analysis of Integrated Circuits (IPFA)*, Pulau Pinang, Malaysia, 2023, pp. 1-6, *doi: 10.1109/IPFA58228.2023.10249113*.

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- [5] K. Soundrapandiyan, S. K. Vishvakarma, and B. S. Reniwal, "Enabling Energy-Efficient In-Memory Computing with Robust Assist-Based Reconfigurable Sense Amplifier in SRAM Array," *IEEE Journal on Emerging and Selected Topics in Circuits and Systems*, vol. 13, no. 1, pp. 445–455, Mar. 2023.
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